## Supporting Information

## Luminescence Mechanism in hydrogenated Silicon Quantum Dots with Single Oxygen Ligand

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|  | $\boldsymbol{m}$-Hn | $m-\mathrm{D}-\mathrm{O}_{1}$ | $m-E-O_{1}$ | $m-\mathrm{D}+\mathbf{E}$ |
| :---: | :---: | :---: | :---: | :---: |
| 1.1 nm |  |  |  |  |
| 1.3 nm |  |  |  |  |
| 1.7 nm |  |  |  |  |
| 2.0 nm |  |  |  |  |

Figure S1. Structure of Si-QDs with different diameter and different passivation configurations.

|  | HOMO | LUMO | HOMO-1 | LUMO +1 |
| :---: | :---: | :---: | :---: | :---: |
| 1.1 nm |  |  |  |  |
| 1.3 nm |  |  |  |  |
| 1.7 nm |  |  |  |  |
| 2.0 nm |  |  |  |  |

Figure S2. HOMO, LUMO, HOMO-1, and LUMO+1 real space distribution of m-D+E Si-QDs.


Figure S3. Emission spectrum from first singlet excited to ground state for various smaller Si-QDs with more than one oxygen atoms. (a) double bonded, (b) epoxide ring bonded
(a)

(b)

(c)

(d)

(e)

(f)

(g)

(h)

(i)

(j)

(k)

(1)


(n)

Electron density distribution Hole density distribution

Figure S4. Electron and hole distribution of Si-QDs with more than one oxygen atoms, in which cyan regions represent electron distribution and mag regions represent hole distribution. (a) 1.1-D$\mathrm{O}_{1}$, (b) 1.1-D-O ${ }_{2}$, (c) 1.1-D-O6, (d) 1.3-D-O $\mathrm{O}_{1}$, (e) 1.3-D-O2, (f) 1.3-D-O $\mathrm{O}_{3}$, (g) 1.3-D-O6, (h) 1.3-D$\mathrm{O}_{8}$, (i) 1.1-E-O ${ }_{1}$, (j) 1.1-E-O $\mathrm{O}_{2}$, (k)1.1-E-O $\mathrm{E}_{6}$, (1)1.3-E-O $\mathrm{O}_{1}$, (m)1.3-E-O $\mathrm{O}_{6}$, (n)1.3-E-O

